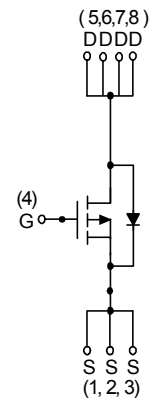
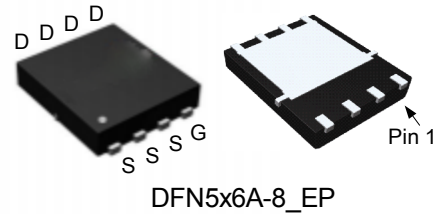


Features

- -40V/-55A,
 $R_{DS(ON)} = 5.1m\Omega$ (typ.) @ $V_{GS} = -20V$
 $R_{DS(ON)} = 6m\Omega$ (typ.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 9.5m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Pin Description



P-Channel MOSFET

Applications

- Power Management in LCD TV Inverter.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		-40	V
V_{GSS}	Gate-Source Voltage		± 25	
I_D^a	Continuous Drain Current ($V_{GS} = -10\text{V}$)	$T_A = 25^\circ\text{C}$	-17	A
		$T_A = 70^\circ\text{C}$	-14	
I_{DP}^a	300 μs Pulsed Drain Current Tested	$T_A = 25^\circ\text{C}$	-69	
I_D^c	Continuous Drain Current ($V_{GS} = -10\text{V}$)	$T_C = 25^\circ\text{C}$	-55	
		$T_C = 100^\circ\text{C}$	-35	
I_{DP}^c	300 μs Pulsed Drain Current Tested	$T_C = 25^\circ\text{C}$	-222	
I_S^c	Diode Continuous Forward Current		-27	mJ
I_{AS}^b	Avalanche Current, Single pulse	$L = 0.5\text{mH}$	-21	
E_{AS}^b	Avalanche Energy, Single pulse	$L = 0.5\text{mH}$	110	$^\circ\text{C}$
T_J	Maximum Junction Temperature		150	
T_{STG}	Storage Temperature Range		-55 to 150	W
P_D^a	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	5	
		$T_A = 70^\circ\text{C}$	3.2	
P_D^c	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	52	
		$T_C = 100^\circ\text{C}$	20	
$R_{\theta JA}^a$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	25	$^\circ\text{C/W}$
		Steady State	60	
$R_{\theta JC}^c$	Thermal Resistance-Junction to Case	Steady State	2.4	

Note a : Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$. $R_{\theta JA}$ steady state $t = 999\text{s}$.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J = 25^\circ\text{C}$).

Note c : The power dissipation P_D is based on $T_{J(MAX)} = 150^\circ\text{C}$, and it is useful for reducing junction-to-case thermal resistance ($R_{\theta JC}$) when additional heat sink is used.

Electrical Characteristics (T_A = 25°C unless otherwise noted)

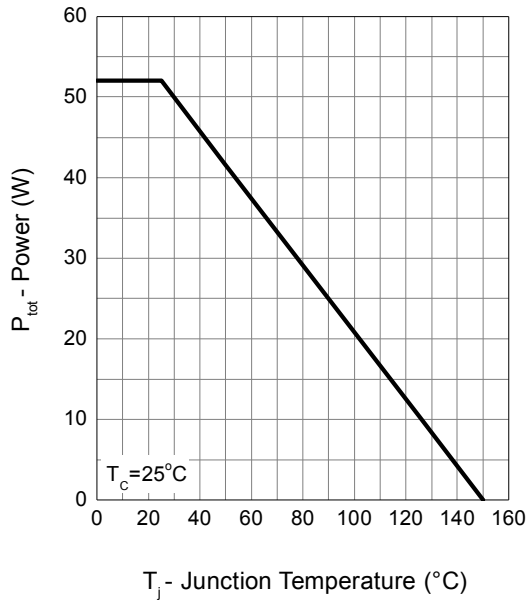
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-32V, V _{GS} =0V T _J =85°C	-	-	-1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.5	-2	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-20V, I _{DS} =-25A V _{GS} =-10V, I _{DS} =-25A V _{GS} =-4.5V, I _{DS} =-15A	- - -	5.1 6 9.5	6.5 7.9 13.5	mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.75	-1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-25A, dI _{SD} /dt=100A/μs	-	23	-	ns
Q _{rr}	Reverse Recovery Charge		-	10	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	3.8	7.6	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-20V, Frequency=1.0MHz	-	2780	3614	pF
C _{oss}	Output Capacitance		-	426	-	
C _{rss}	Reverse Transfer Capacitance		-	331	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-20V, R _L =20Ω, I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	17	31	ns
t _r	Turn-on Rise Time		-	14	25	
t _{d(OFF)}	Turn-off Delay Time		-	59	106	
t _f	Turn-off Fall Time		-	22	40	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-10V, I _{DS} =-25A	-	59	83	nC
Q _{gs}	Gate-Source Charge		-	8	-	
Q _{gd}	Gate-Drain Charge		-	16	-	

Note d : Pulse test; pulse width≤300μs, duty cycle≤2%.

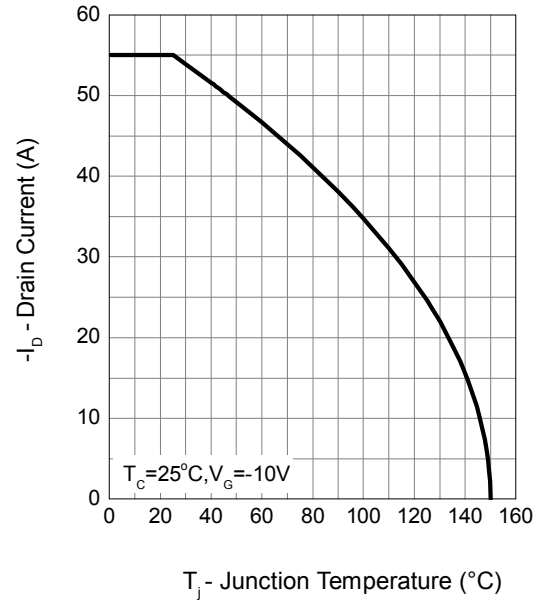
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

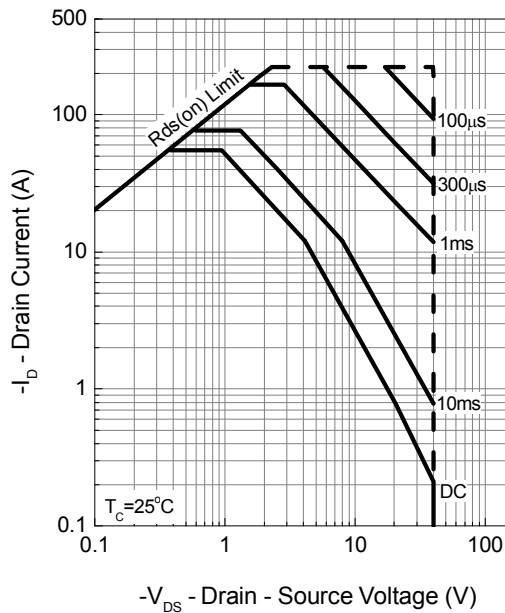
Power Dissipation



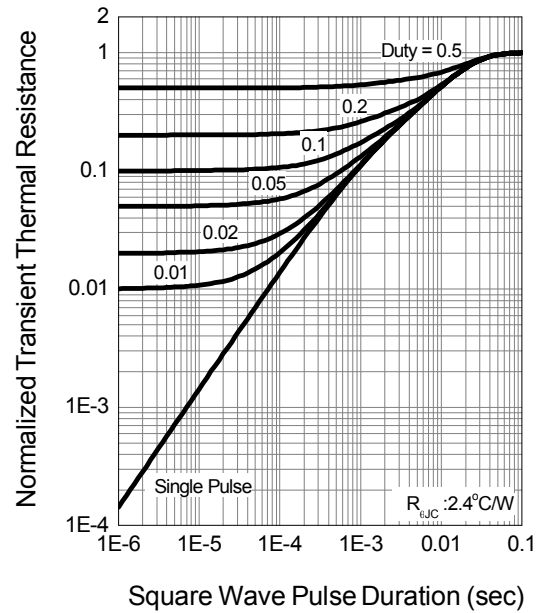
Drain Current



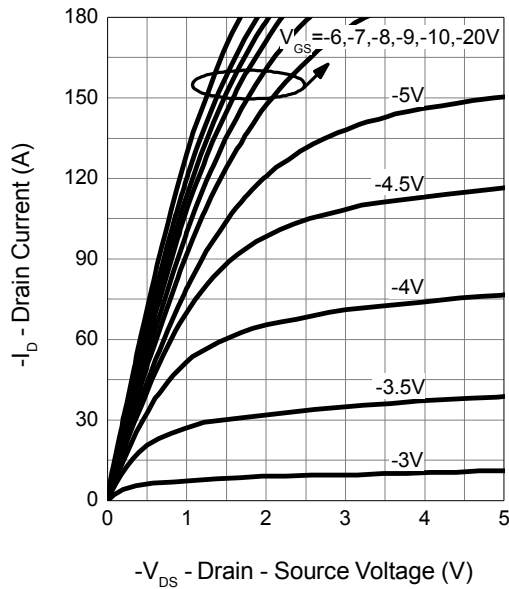
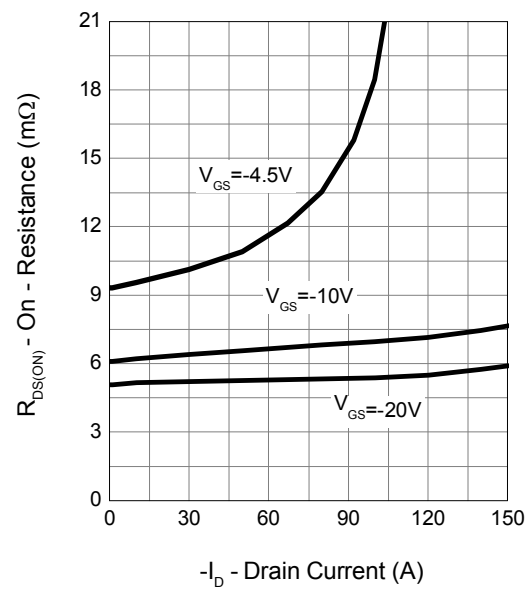
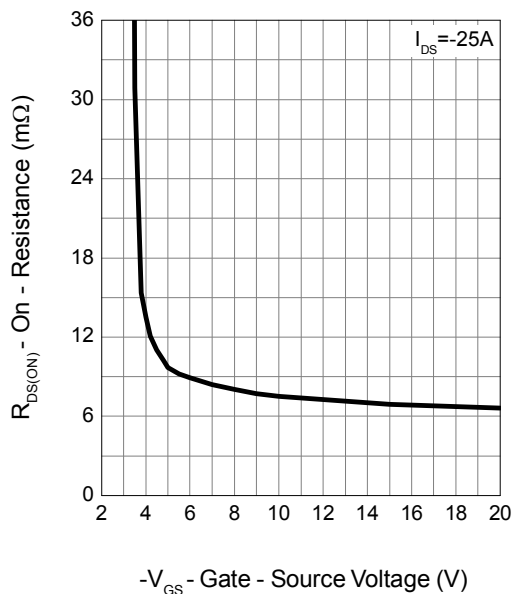
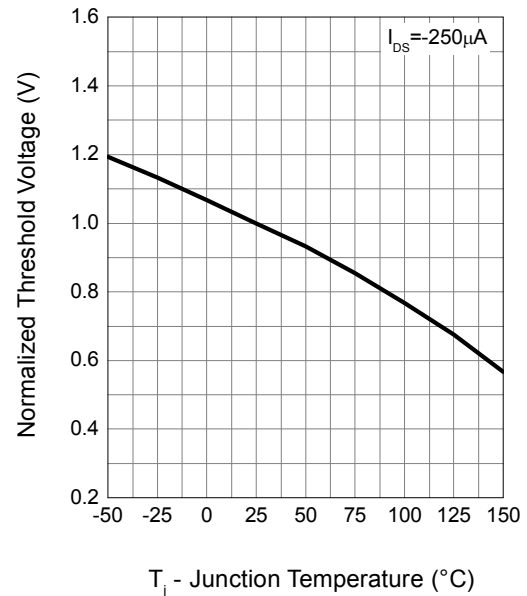
Safe Operation Area



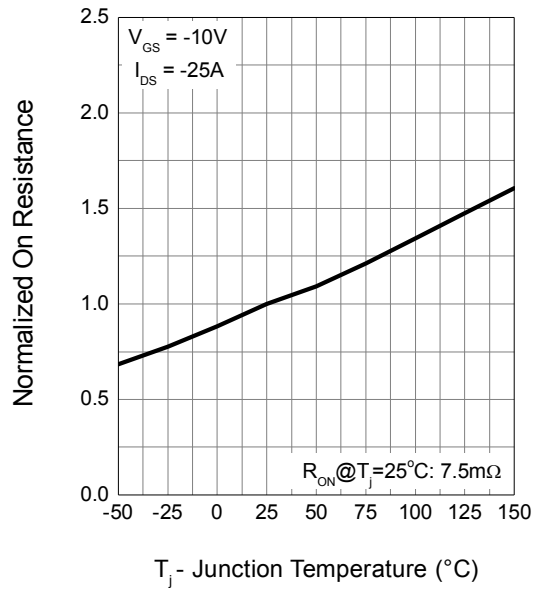
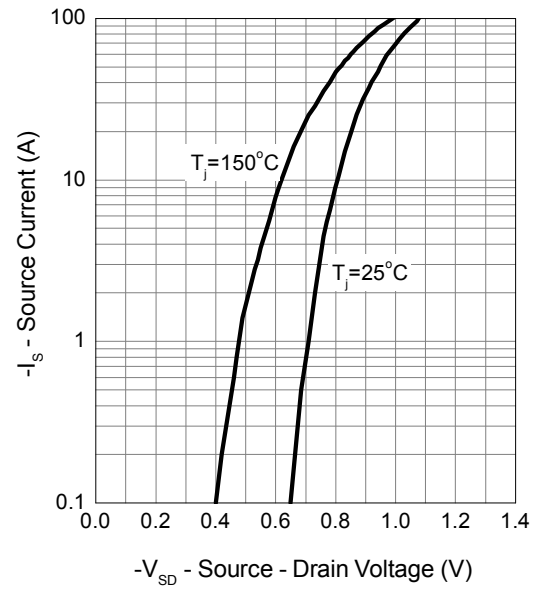
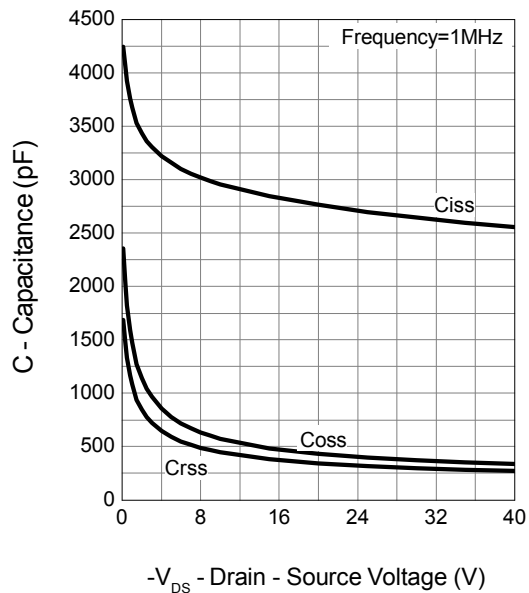
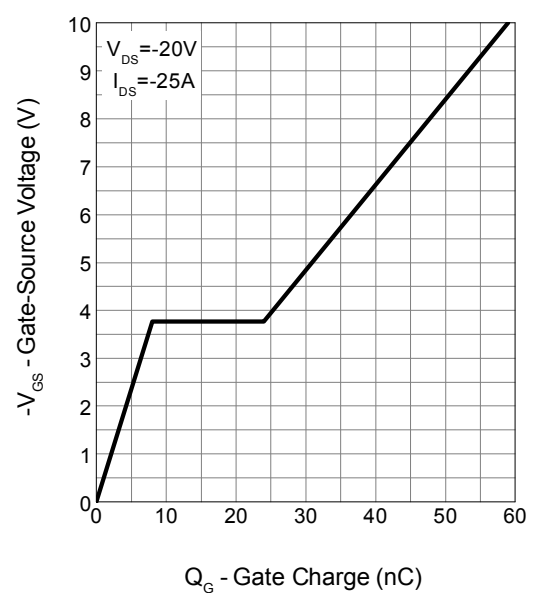
Thermal Transient Impedance



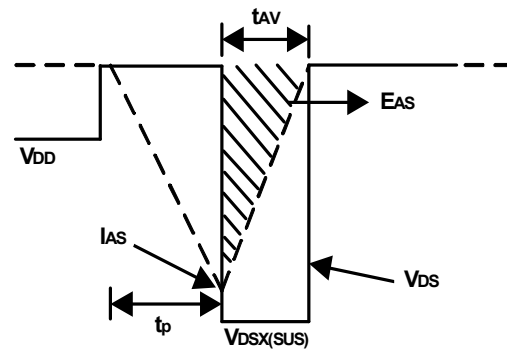
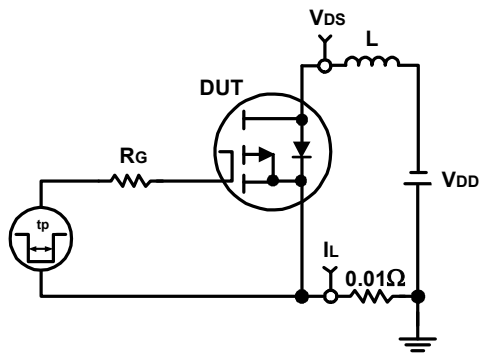
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


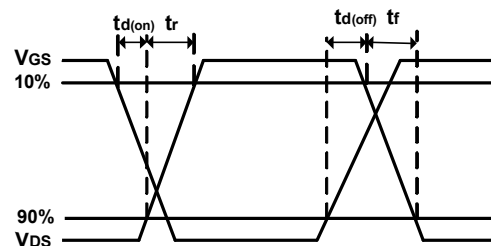
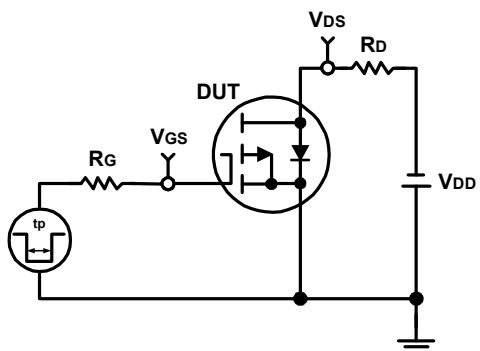
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance

Source-Drain Diode Forward

Capacitance

Gate Charge


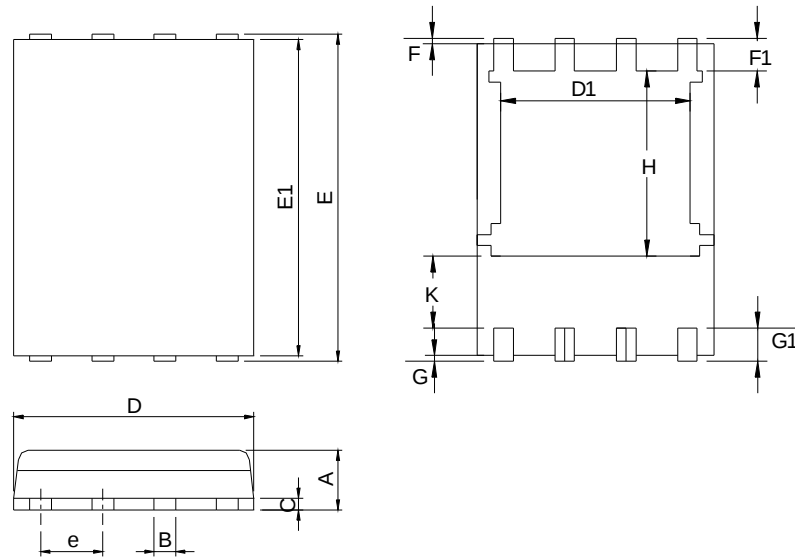
Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



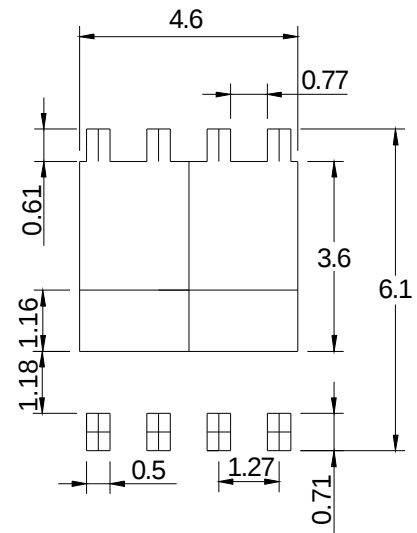
Package Information

DFN5x6-8


SYMBOL	DFN5x6-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.
Mold flash or protrusions shall not exceed 10 mil.

RECOMMENDED LAND PATTERN



UNIT: mm